Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a 3-lead TO220 plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series BT" triac will commutate the full RMS current at the maximum rated junction temperature without the aid of a snubber where "high junction operating temperature capability" is required.

2. Features and benefits

- · High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- · Planar passivated for voltage ruggedness and reliability
- · High junction operating temperature capability
- · Triggering in three quadrants only
- · 3Q technology for improved noise immunity
- High voltage capability

3. Applications

- · Applications subject to high temperature
- Electronic thermostats (heating and cooling)
- · High power motor controls e.g. washing machines and vacuum cleaners
- · Rectifier-fed DC inductive loads e.g. DC motors and solenoids

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit
Absolute	maximum rating					
V_{DRM}	repetitive peak off-state voltage		(600		V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	1	40		А
T _j	junction temperature		1	50		°C
$I_{T(RMS)}$	RMS on-state current	full sine wave; T _{mb} ≤ 126 °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	16		А	
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics			'		
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$	2	-	50	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{ G-;} $ $T_j = 25 \text{ °C; } Fig. 7$	2	-	50	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	2	-	50	mA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	N.I.
2	T2	main terminal 2		T2—T1
3	G	gate		`G sym051
mb	Т2	mounting base; main terminal 2	1 2 3 E d	

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BTA316-600BT	TO220	BTA316-600BT,127	Tube	50	TO220E (E)	26-April-2019
					SOT78 (d)	13-Jun-2008

7. Marking

Table 4. Marking codes

Type number	Marking codes		
	Assembly factory: E	Assembly factory: d	
BTA316-600BT	BTA316 600BT PJExxxx xx	BTA316 600BT PJdxxxx xx	

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		600	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 126 °C; Fig 1; Fig 2; Fig 3	16	А
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig 4; Fig 5	140	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	150	А
l ² t	I ² t for fusing	t _P = 10 ms; SIN	98	A ² s
dl _⊤ /dt	rate of rise of on-state current	$I_T = 20 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A}/\mu\text{s}$	100	A/µs
I _{GM}	peak gate current		2	А
P _{GM}	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		150	°C

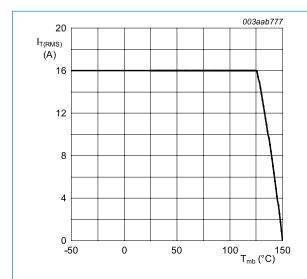
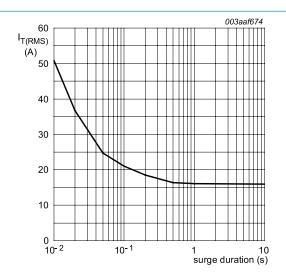
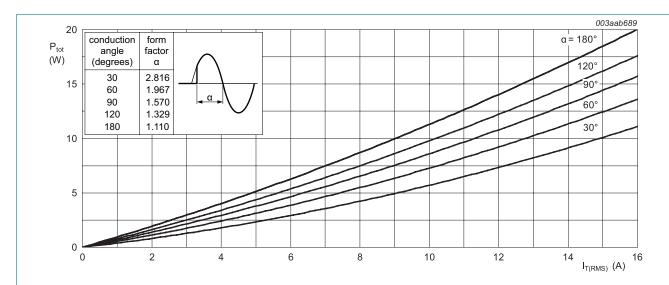


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



 $f = 50 \text{ Hz}; T_{mb} = 126 ^{\circ}\text{C}$

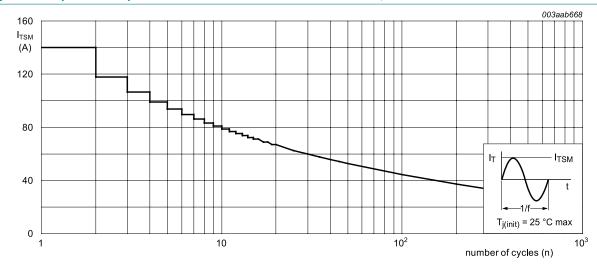
Fig. 2. RMS on-state current as a function of surge duration; maximum values



 α = conduction angle

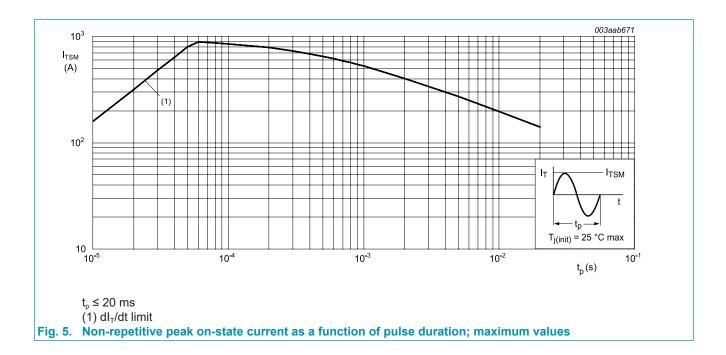
a = form factor = $I_{T(RMS)}/I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

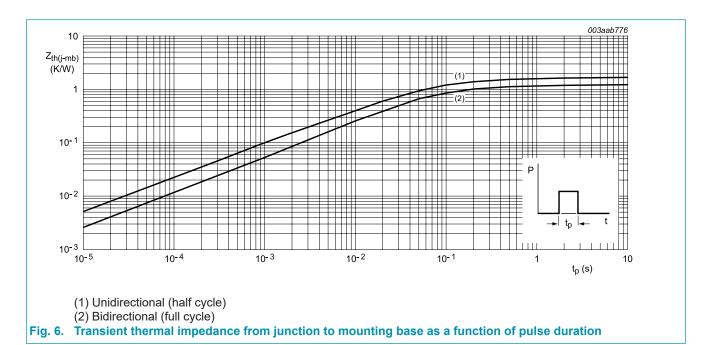
Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



9. Thermal characteristics

Table 6. Thermal characteristics

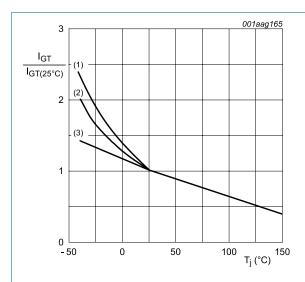
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance	full cycle; Fig 6	-	-	1.2	K/W
	from junction to mounting base	half cycle; Fig 6	-	-	1.7	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics		·			
I _{GT} gate	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+; $ $T_j = 25 \text{ °C}; Fig. 7$	2	-	50	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{ G-;} $ $T_j = 25 \text{ °C; } Fig. 7$	2	-	50	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G-;} $ $T_j = 25 \text{ °C; } Fig. 7$	2	-	50	mA
I _L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	60	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	90	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	60	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	60	mA
V _T	on-state voltage	I _T = 18 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.8	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 150 °C	0.25	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 150 °C	-	0.24	1.2	mA
Dynamic	characteristics		'			
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	600	-	-	V/µs
dI _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 16 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit	8	-	-	A/ms





- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

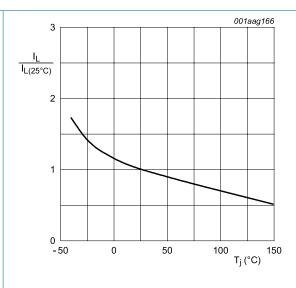


Fig. 8. Normalized latching current as a function of junction temperature

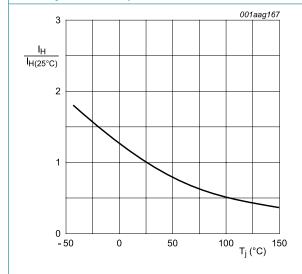
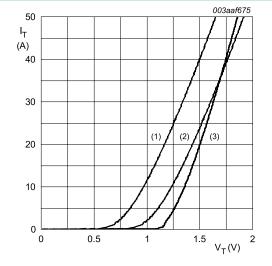


Fig. 9. Normalized holding current as a function of junction temperature



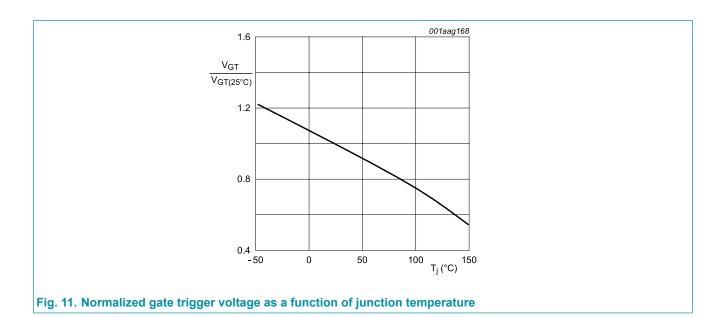
 $V_o = 1.024 \text{ V}; R_s = 0.021 \Omega$

(1) T_i = 150 °C; typical values

(2) $T_j = 150$ °C; maximum values

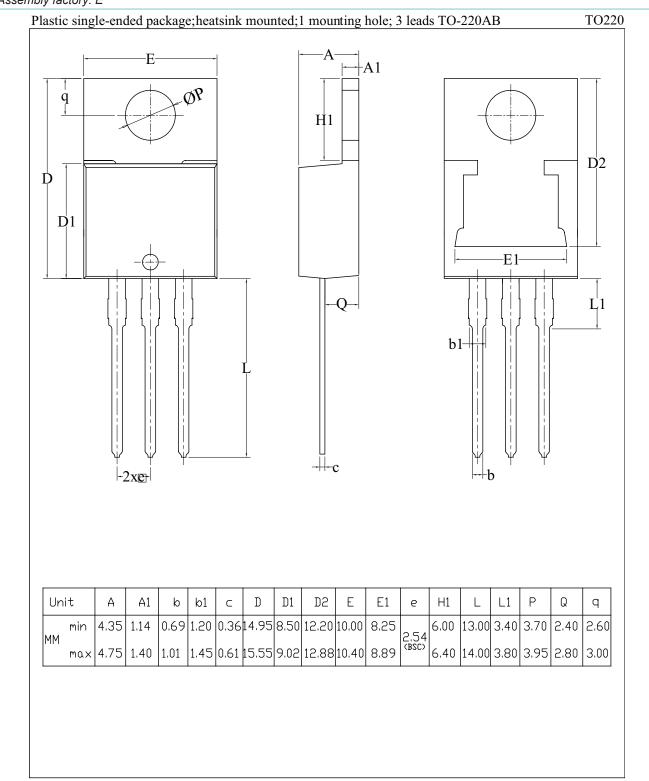
(3) T_i = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

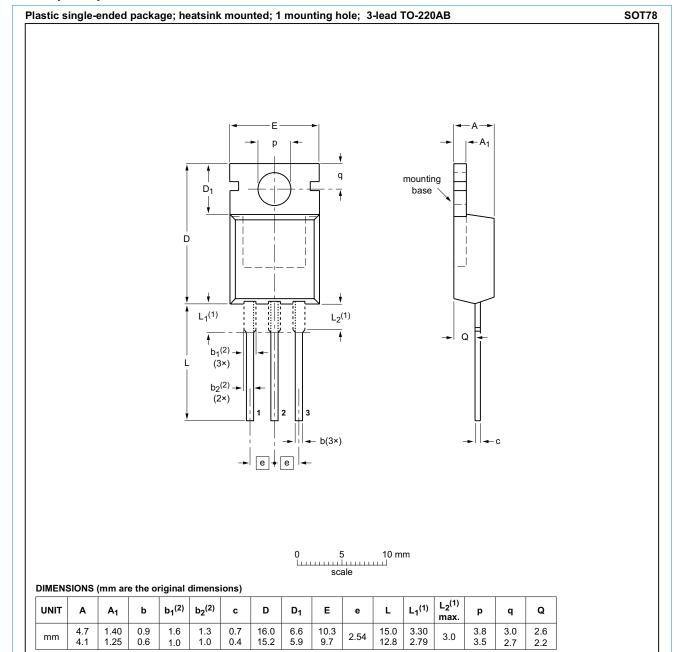


11. Package outline

Assembly factory: E



Assembly factory: d



Notes

- Lead shoulder designs may vary.
 Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN ISSUE DA	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	1330E DATE
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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